In the Claims

Please cancel Claims 22,24,25,34-37 and 40.

Please amend Claim 26.

Listing of Claims

Claims 1-25 (canceled)

26. (currently amended) A phase change memory structure comprising:

a substrate comprising a conductive area;

a spacer comprising a phase changing material sensitive to temperature and having a partially exposed sidewall region at the spacer upper portion defining a phase change memory element contact area; and

an upper conductive electrode on ~~the electrode~~ said phase change memory element contact area~~.~~; wherein a spacer bottom portion partially overlaps the conductive area~~.~~ and said upper conductive electrode at least partially overlaps said conductive area.

27. (original)The phase change memory structure of claim 26, wherein the upper conductive electrode comprises a material selected from the group consisting of W, TiN, TiW, TiAl, TiAlN, and combinations thereof.

28. (previously presented) A phase change memory structure comprising:

a substrate comprising a conductive area;

a spacer having a partially exposed sidewall region at the spacer upper portion defining a phase change memory element contact area;

wherein the spacer comprises a conductive material and a spacer bottom portion partially overlaps the conductive area.

29. (original) The phase change memory structure of claim 28, wherein the conductive material comprises a material selected from the group consisting of W, TiN, TiW, TiAl, TiAlN, and combinations thereof.

30. (original) The phase change memory structure of claim 28, further comprising:

a phase changing memory element sensitive to temperature on the electrode contact area; and,

an upper conductive electrode on the phase changing memory element.

31. (original) The phase change memory structure of claim 30, wherein the phase changing memory element comprises a chalcogenide.

32. (original) The phase change memory structure of claim 31, wherein the chalcogenide comprises a material selected from

the group consisting of Ge, Te, and Sb and their alloy system.

33. (original) The phase change memory structure of claim 30, wherein the upper conductive electrode comprises a material selected from the group consisting of W, TiN, TiW, TiAl, TiAlN, and combinations thereof.

Claims 34-40 (canceled)